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ABSTRACT OF THE DISCLOSUREMETHOD FOR DEPOSITING A SILICON-CONTAINING DIELECTRIC
MATERIAL ON COPPER

The invention concerns a method for depositing a dielectric material (11) on copper (15) apparent on the surface of a structure (10), entailing the following steps:

- 5 placing the structure (10) in a depositing chamber of CVD type (Chemical Vapour Deposition),
 adding to the chamber a first gas forming a precursor for the formation of the dielectric material and containing an element able to contaminate copper,
10 adding to the chamber a second gas containing a chemical element intended, together with the element contained in the first gas and able to contaminate copper, to form said dielectric material (11), the second gas being able to react with the first gas to
15 give the deposit of dielectric material (11),
 performing the deposit of dielectric material from the first gas and the second gas,
 characterized in that the method comprises a step for adding a third gas able to prevent the contamination of
20 copper by said element contained in the first gas.

Fig. 3

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